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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

August 2014

FQA28N50

N-Channel QFET® MOSFET

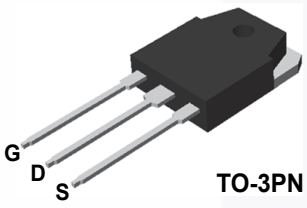
500 V, 28.4 A, 160 mΩ

Features

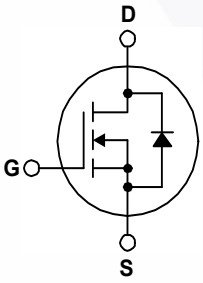
- 28.4 A, 500 V, $R_{DS(on)}$ = 160 mΩ (Max.) @ V_{GS} = 10 V, I_D = 14.2 A
- Low Gate Charge (Typ. 110 nC)
- Low Crss (Typ. 60 pF)
- 100% Avalanche Tested
- RoHS compliant

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, power factor correction, electronic lamp ballast based on half bridge.



TO-3PN



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA28N50	Unit
V_{DSS}	Drain-Source Voltage		500	V
I_D	Drain Current - Continuous (T_C = 25°C)		28.4	A
	- Continuous (T_C = 100°C)		18	A
I_{DM}	Drain Current - Pulsed	(Note 1)	113.6	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	1300	mJ
I_{AR}	Avalanche Current	(Note 1)	28.4	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	31	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P_D	Power Dissipation (T_C = 25°C)		310	W
	- Derate above 25°C		2.5	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.4	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA28N50	FQA28N50	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	500	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.5	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 500 V, V_{GS} = 0 V	--	--	1	μA
		V_{DS} = 400 V, T_C = 125°C	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 14.2 A	--	0.126	0.16	Ω
g_{FS}	Forward Transconductance	V_{DS} = 50 V, I_D = 14.2 A	--	28	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	4300	5600	pF
C_{oss}	Output Capacitance		--	640	830	pF
C_{rss}	Reverse Transfer Capacitance		--	60	80	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 250 V, I_D = 28.4 A, R_G = 25 Ω (Note 4)	--	100	210	ns
t_r	Turn-On Rise Time		--	290	590	ns
$t_{d(off)}$	Turn-Off Delay Time		--	250	510	ns
t_f	Turn-Off Fall Time		--	175	360	ns
Q_g	Total Gate Charge	V_{DS} = 400 V, I_D = 28.4 A, V_{GS} = 10 V (Note 4)	--	110	140	nC
Q_{gs}	Gate-Source Charge		--	26	--	nC
Q_{gd}	Gate-Drain Charge		--	52	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	28.4	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	113.6	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 28.4 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 28.4 A, dI_F / dt = 100 A/μs	--	440	--	ns
Q_{rr}	Reverse Recovery Charge		--	5.7	--	μC

Notes :

1. Repetitive rating : pulse width limited by maximum junction temperature.
2. L = 2.9 mH, I_{AS} = 28.4 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 28.4 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Characteristics

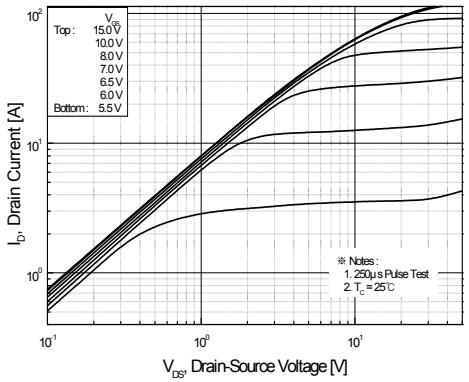


Figure 1. On-Region Characteristics

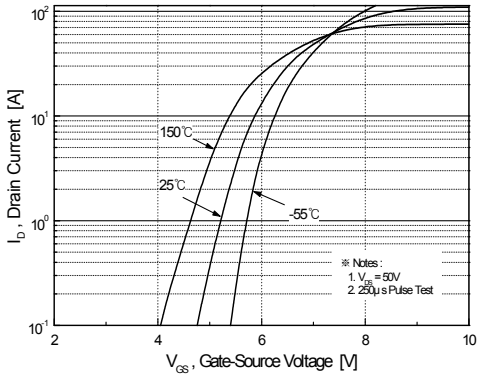


Figure 2. Transfer Characteristics

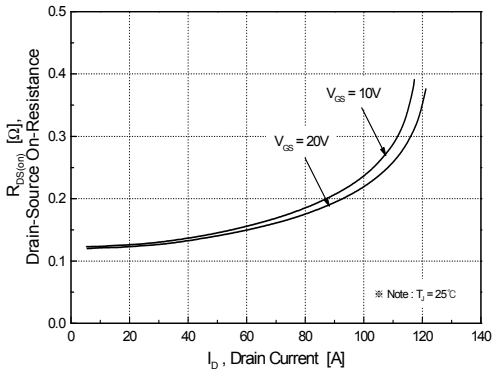


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

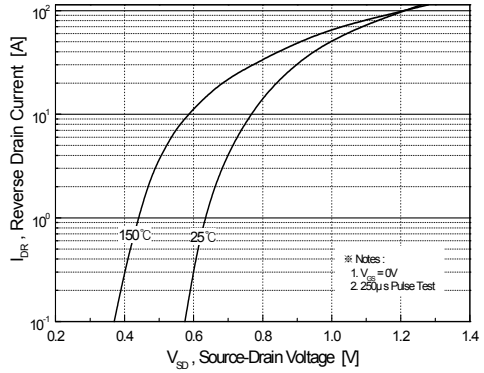


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

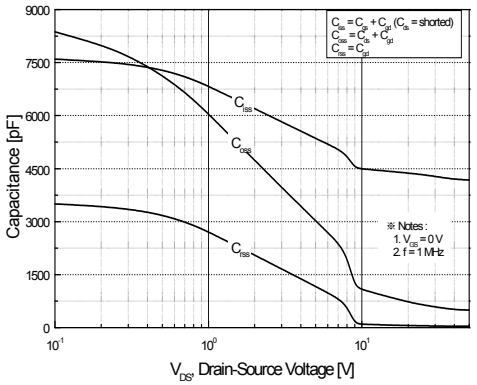


Figure 5. Capacitance Characteristics

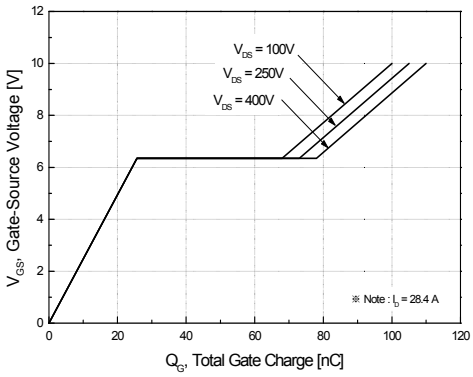


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

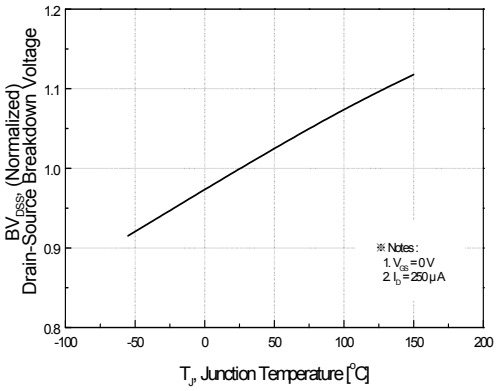


Figure 7. Breakdown Voltage Variation vs. Temperature

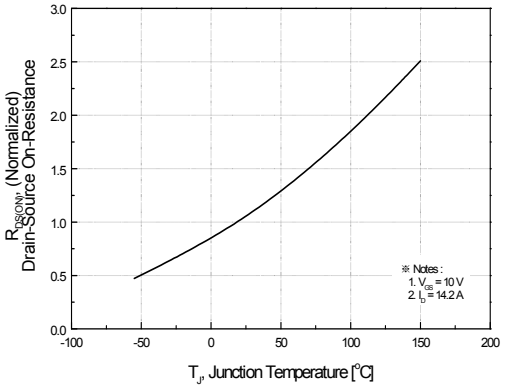


Figure 8. On-Resistance Variation vs. Temperature

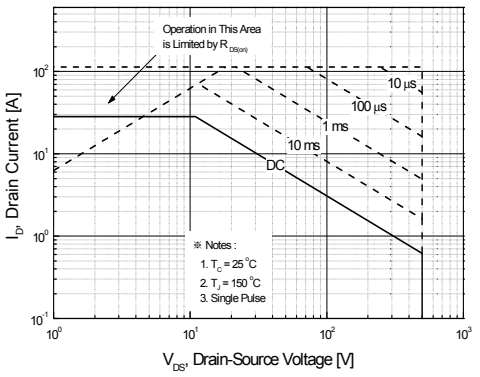


Figure 9. Maximum Safe Operating Area

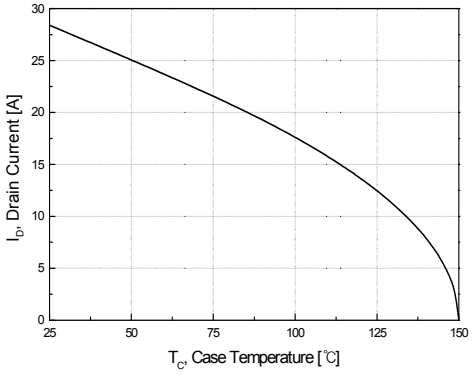


Figure 10. Maximum Drain Current vs. Case Temperature

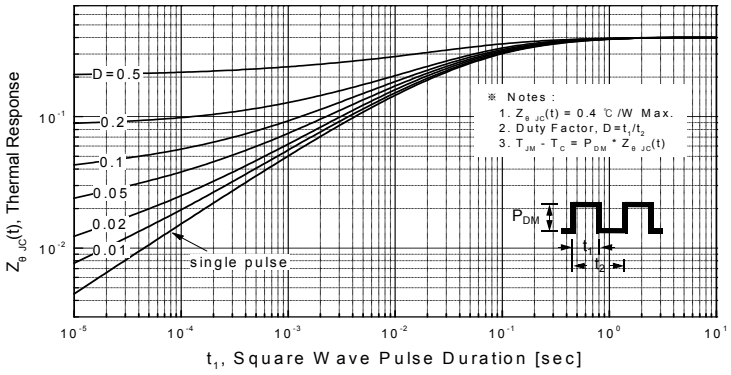


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

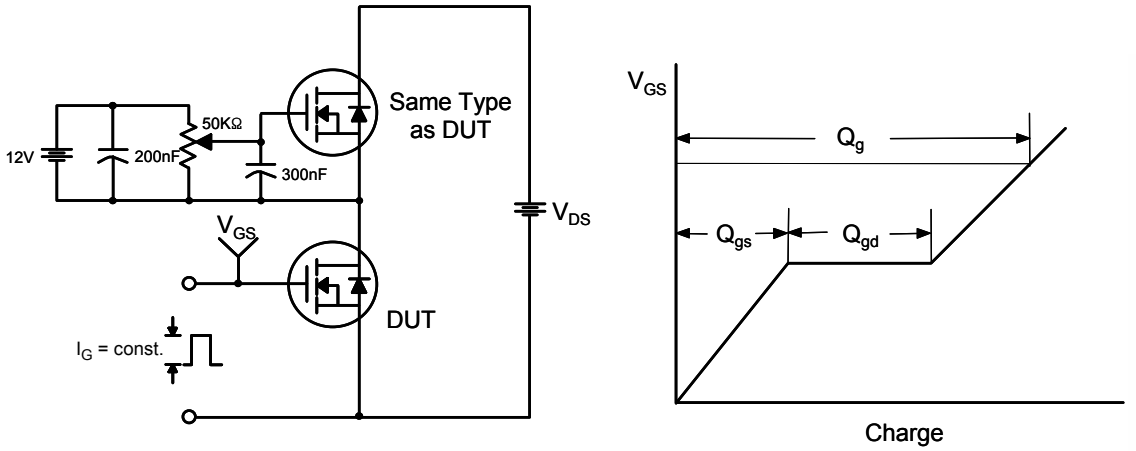


Figure 13. Resistive Switching Test Circuit & Waveforms

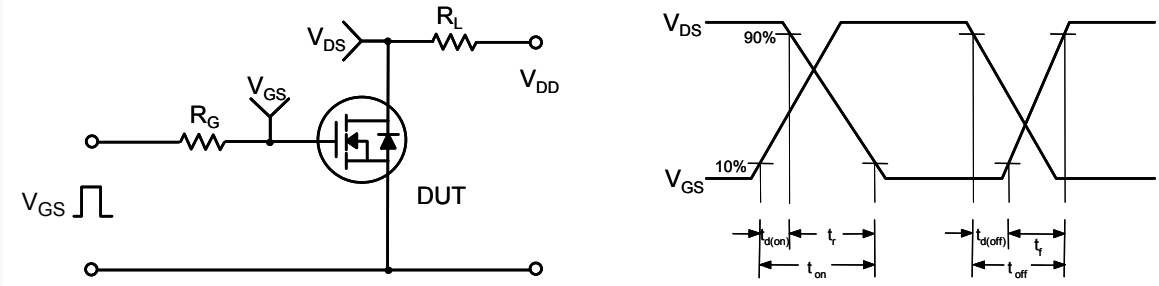


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

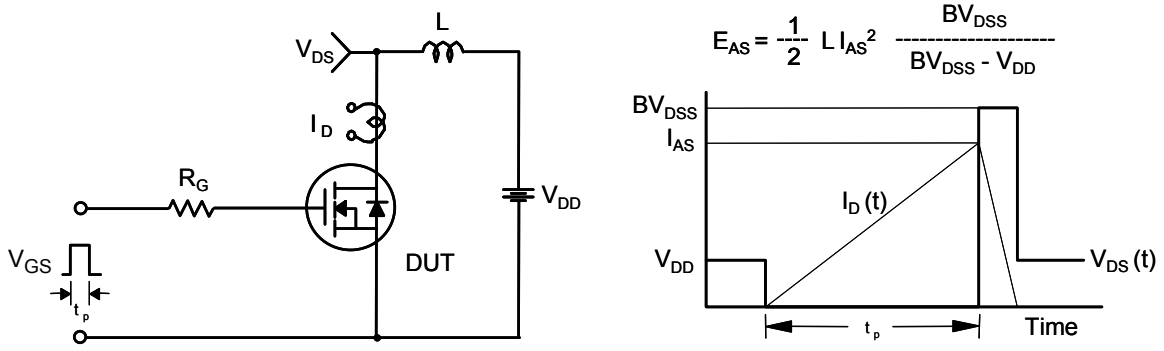
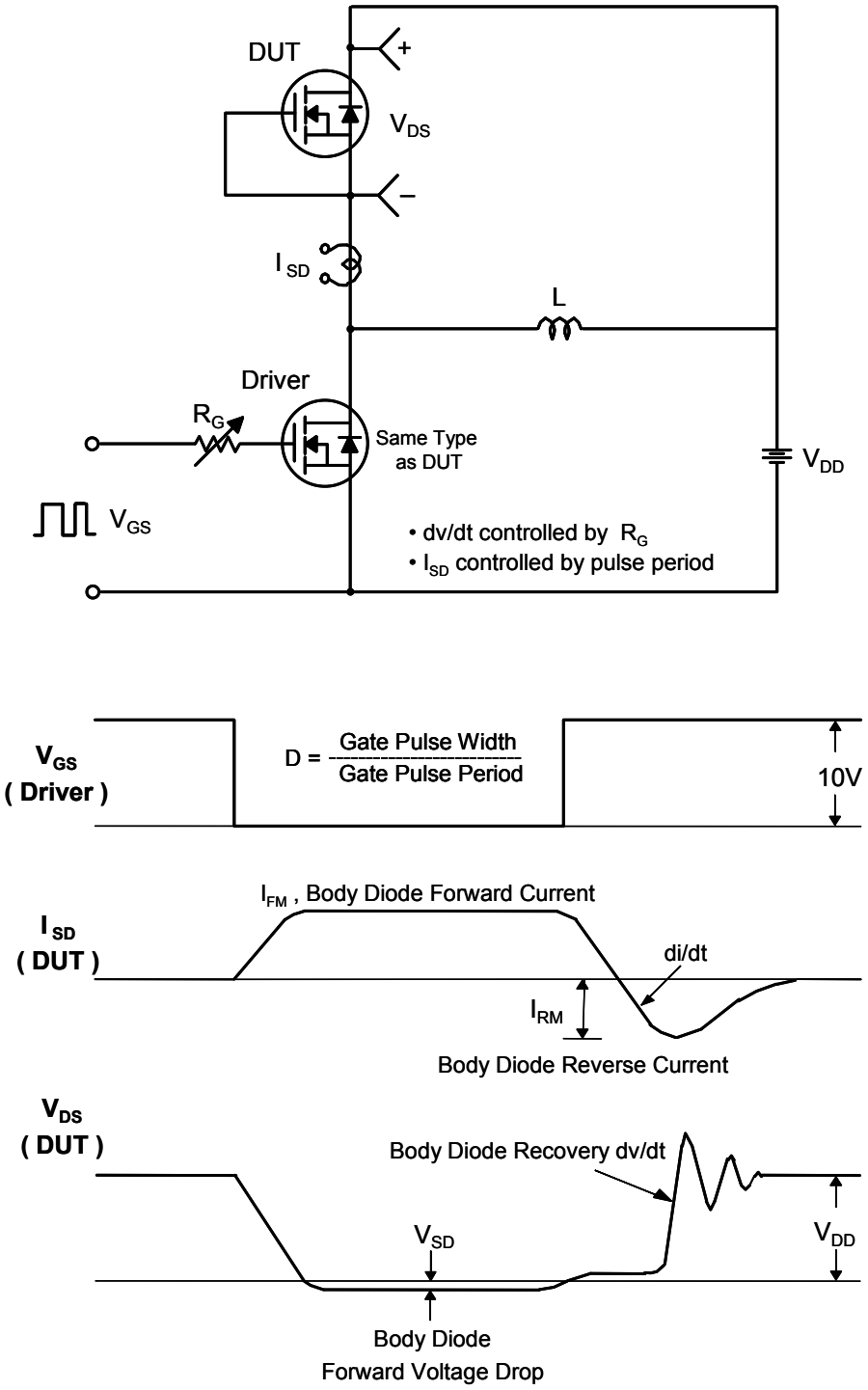
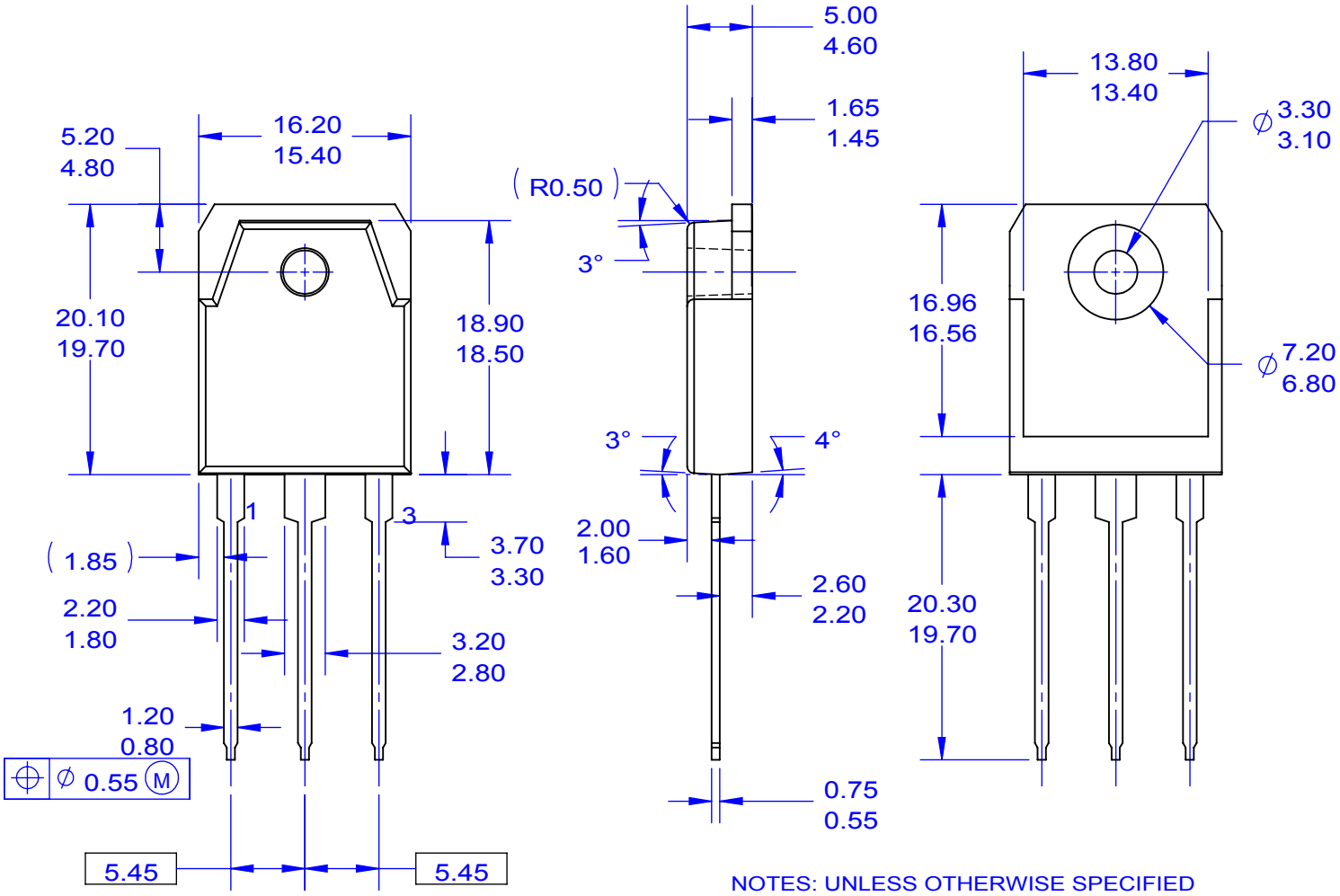
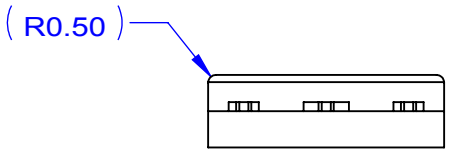


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms







NOTES: UNLESS OTHERWISE SPECIFIED

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B) ALL DIMENSIONS ARE IN MILLIMETERS.
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